

# 2N6344A, 2N6348A, 2N6349A

Preferred Device

## Triacs

### Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in all Four Quadrants
- For 400 Hz Operation, Consult Factory
- 8 Ampere Devices Available as 2N6344 thru 2N6349
- Device Marking: Logo, Device Type, e.g., 2N6344A, Date Code

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
*Peak Repetitive Off-State Voltage <sup>(1)</sup> (Gate Open, $T_J = -40$ to $+110^\circ\text{C}$ , Sine Wave 50 to 60 Hz, Gate Open) 2N6344A, 2N6348A 2N6349A	$V_{DRM}$ , $V_{RRM}$	600 800	Volts
*On-State RMS Current (Full Cycle Sine Wave 50 to 60 Hz) ( $T_C = +80^\circ\text{C}$ ) ( $T_C = +95^\circ\text{C}$ )	$I_T(\text{RMS})$	12 6.0	A
*Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, $T_C = +80^\circ\text{C}$ ) Preceded and followed by rated current	$I_{TSM}$	100	A
Circuit Fusing Consideration ( $t = 8.3$ ms)	$I^2t$	59	$\text{A}^2\text{s}$
*Peak Gate Power ( $T_C = +80^\circ\text{C}$ , Pulse Width = 2.0 $\mu\text{s}$ )	$P_{GM}$	20	Watts
*Average Gate Power ( $T_C = +80^\circ\text{C}$ , $t = 8.3$ ms)	$P_{G(AV)}$	0.5	Watt
*Peak Gate Current (Pulse Width = 2.0 $\mu\text{s}$ ; $T_C = +80^\circ\text{C}$ )	$I_{GM}$	2.0	A
*Peak Gate Voltage (Pulse Width = 2.0 $\mu\text{s}$ ; $T_C = +80^\circ\text{C}$ )	$V_{GM}$	$\pm 10$	Volts
*Operating Junction Temperature Range	$T_J$	$-40$ to $+125$	$^\circ\text{C}$
*Storage Temperature Range	$T_{stg}$	$-40$ to $+150$	$^\circ\text{C}$

\*Indicates JEDEC Registered Data.

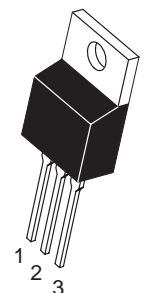
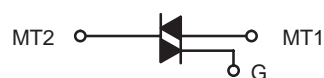
(1)  $V_{DRM}$  and  $V_{RRM}$  for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor

<http://onsemi.com>

### TRIACS 12 AMPERES RMS 600 thru 800 VOLTS



TO-220AB  
CASE 221A  
STYLE 4

#### PIN ASSIGNMENT

1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

#### ORDERING INFORMATION

Device	Package	Shipping
2N6344A	TO220AB	500/Box
2N6348A	TO220AB	500/Box
2N6349A	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.

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## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	$T_L$	260	°C

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in either direction)

Characteristic	Symbol	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

*Peak Repetitive Blocking Current ( $V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{ Gate Open}$ )	$I_{DRM}, I_{RRM}$	—	—	10	$\mu\text{A}$
$T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$		—	—	2.0	mA

## ON CHARACTERISTICS

*Peak On-State Voltage ( $I_{TM} = \pm 17 \text{ A Peak}; \text{ Pulse Width} = 1 \text{ to } 2 \text{ ms}, \text{ Duty Cycle} \leq 2\%$ )	$V_{TM}$	—	1.3	1.75	Volts
Gate Trigger Current (Continuous dc) ( $V_D = 12 \text{ Vdc}, R_L = 100 \text{ Ohms}$ ) MT2(+), G(+) MT2(+), G(—) MT2(—), G(—) MT2(—), G(+) *MT2(+), G(+); MT2(—), G(—) $T_C = -40^\circ\text{C}$ *MT2(+), G(—); MT2(—), G(+), $T_C = -40^\circ\text{C}$	$I_{GT}$	— — — — —	6.0 6.0 10 25	50 75 50 75	mA
Gate Trigger Voltage (Continuous dc) ( $V_D = 12 \text{ Vdc}, R_L = 100 \text{ ohms}$ ) MT2(+), G(+) MT2(+), G(—) MT2(—), G(—) MT2(—), G(+) *MT2(+), G(+); MT2(—), G(—) $T_C = -40^\circ\text{C}$ *MT2(+), G(—); MT2(—), G(+), $T_C = -40^\circ\text{C}$	$V_{GT}$	— — — —	0.9 0.9 1.1 1.4	2.0 2.5 2.0 2.5	Volts
Gate Non-Trigger Voltage ( $V_D = \text{Rated } V_{DRM}, R_L = 10 \text{ k ohms}, T_J = 110^\circ\text{C}$ ) *MT2(+), G(+); MT2(—), G(—); MT2(+), G(—); MT2(—), G(+)	$V_{GD}$	0.2	—	—	Volts
Holding Current ( $V_D = 12 \text{ Vdc}, \text{ Gate Open}$ ) Initiating Current = $\pm 200 \text{ mA}$ $T_C = 25^\circ\text{C}$ * $T_C = -40^\circ\text{C}$	$I_H$	— —	6.0 —	40 75	mA
*Turn-On Time ( $V_D = \text{Rated } V_{DRM}, I_{TM} = 17 \text{ A}, I_{GT} = 120 \text{ mA},$ Rise Time = $0.1 \mu\text{s}$ , Pulse Width = $2 \mu\text{s}$ )	$t_{gt}$	—	1.5	2.0	$\mu\text{s}$

## DYNAMIC CHARACTERISTICS

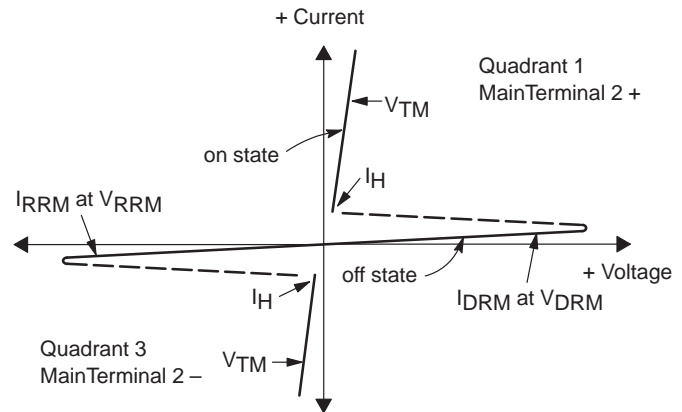
Critical Rate of Rise of Commutation Voltage ( $V_D = \text{Rated } V_{DRM}, I_{TM} = 17 \text{ A}, \text{ Commutating } di/dt = 6.1 \text{ A/ms},$ Gate Unenergized, $T_C = 80^\circ\text{C}$ )	$dv/dt(c)$	—	5.0	—	V/ $\mu\text{s}$
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\*Indicates JEDEC Registered Data.

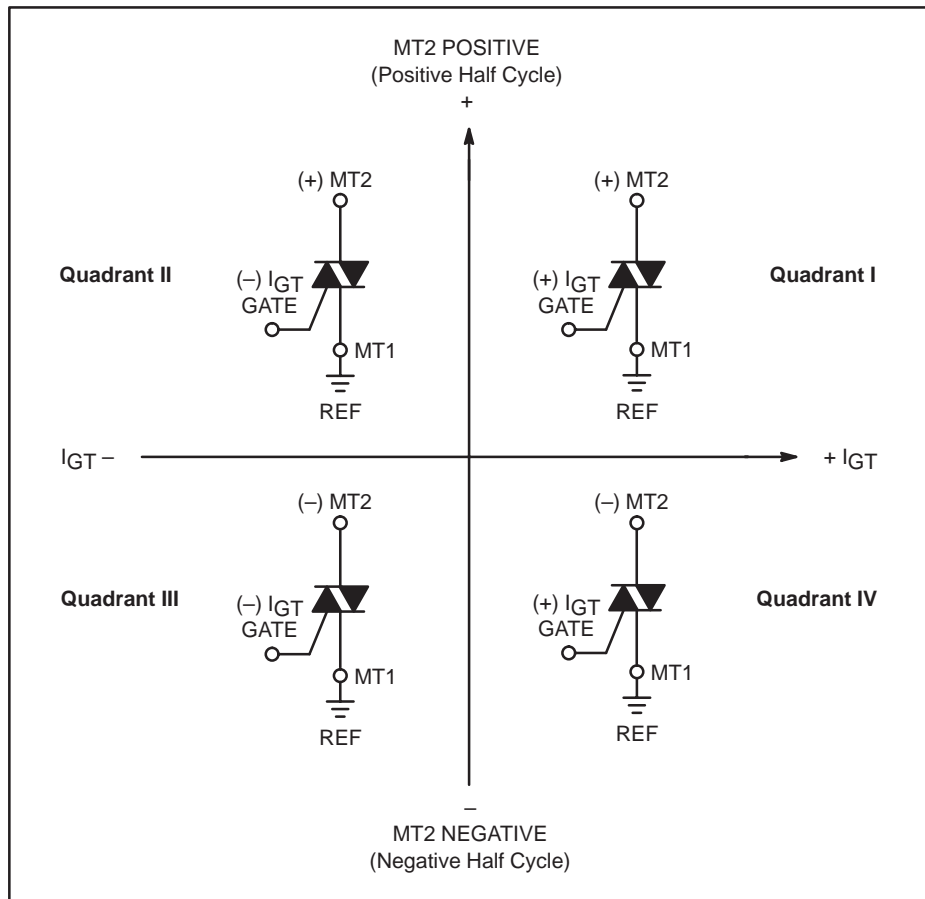
## 2N6344A, 2N6348A, 2N6349A

### Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
$I_H$	Holding Current



### Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

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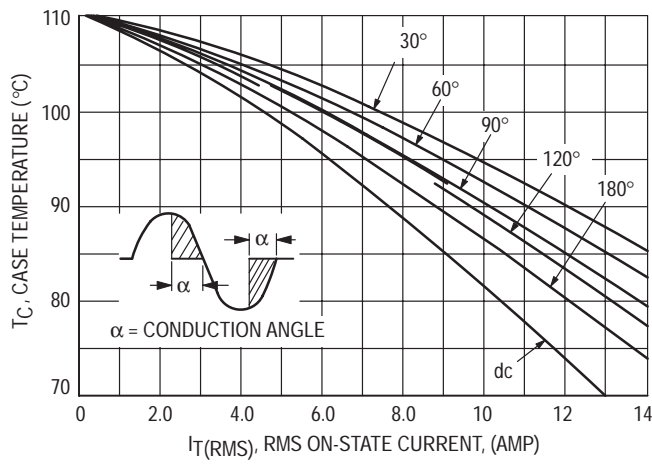


Figure 1. RMS Current Derating

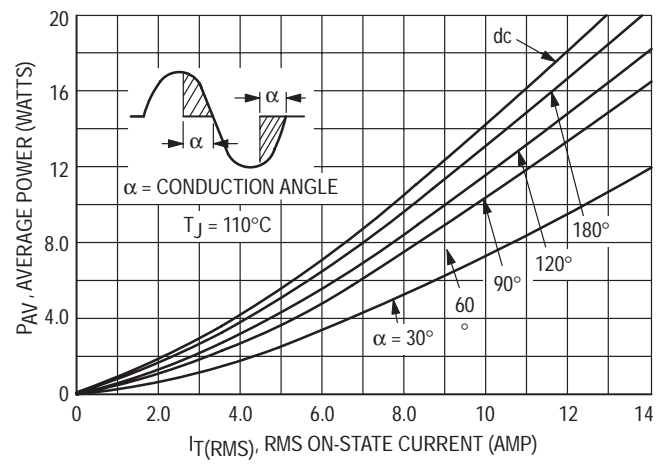


Figure 2. On-State Power Dissipation

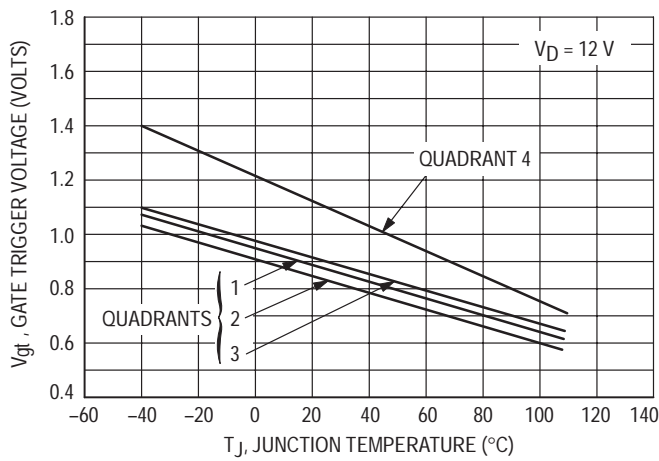


Figure 3. Typical Gate Trigger Voltage

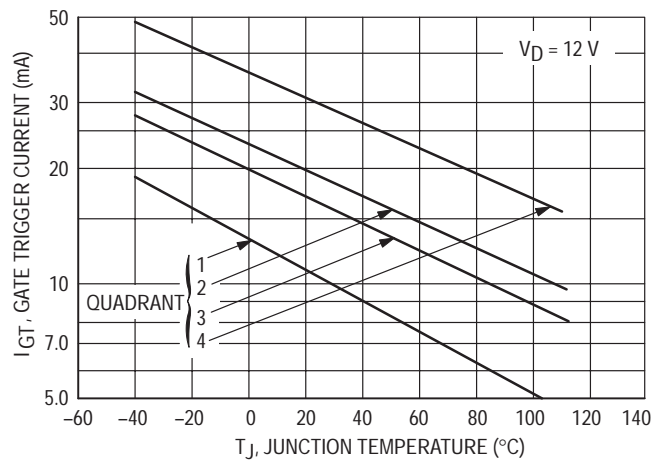


Figure 4. Typical Gate Trigger Current

# 2N6344A, 2N6348A, 2N6349A

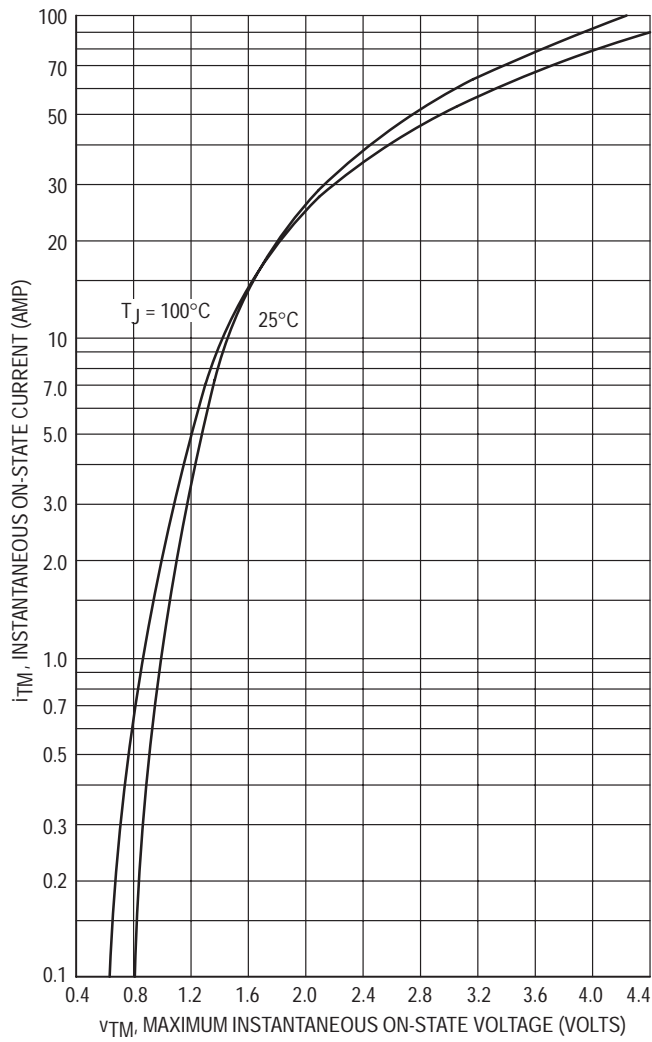


Figure 5. On-State Characteristics

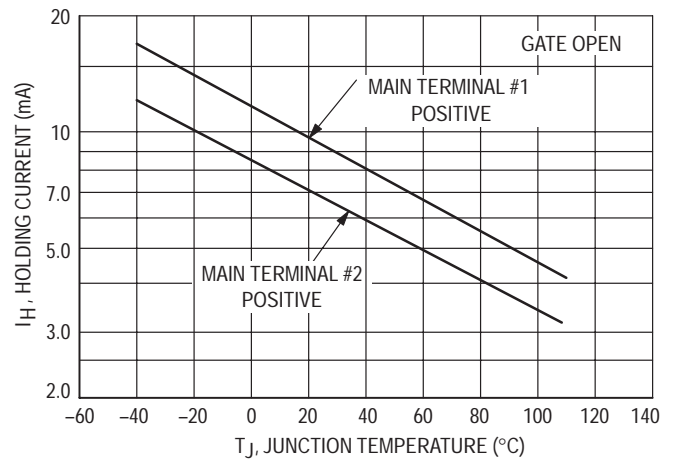


Figure 6. Typical Holding Current

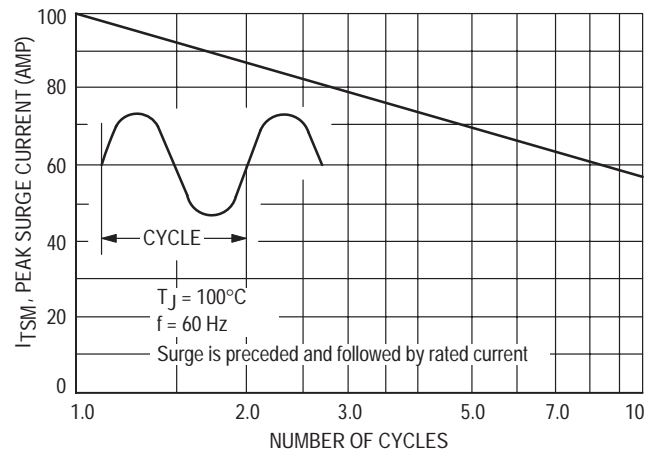


Figure 7. Maximum Non-Repetitive Surge Current

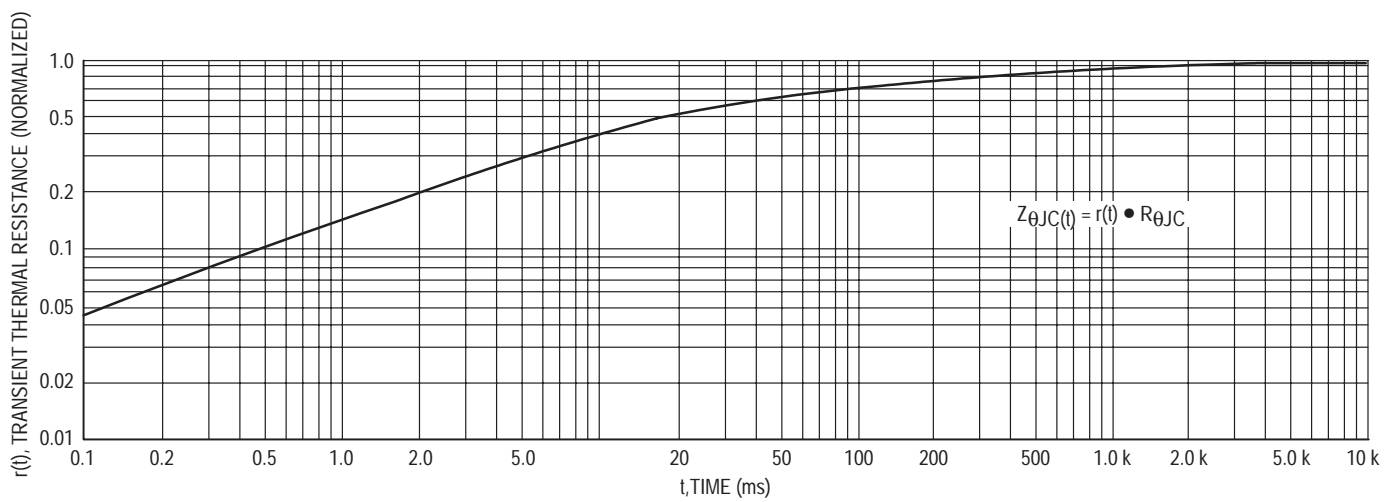
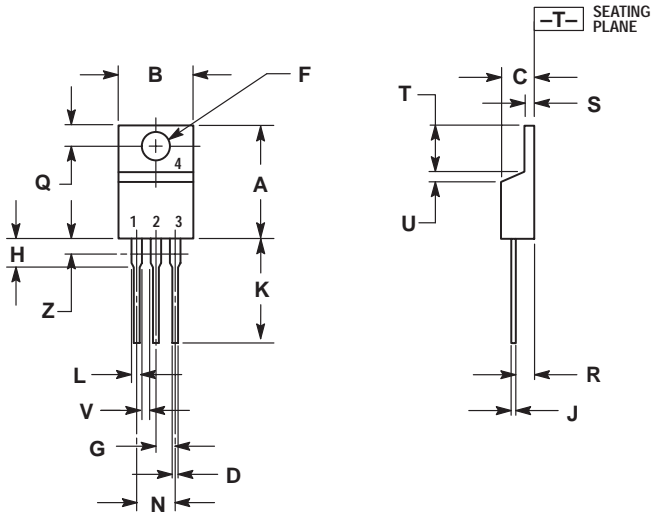


Figure 8. Typical Thermal Response

# 2N6344A, 2N6348A, 2N6349A

## PACKAGE DIMENSIONS

### TO-220AB CASE 221A-07 ISSUE Z



#### NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

#### STYLE 4:

- PIN 1. MAIN TERMINAL 1
- MAIN TERMINAL 2
- GATE
- MAIN TERMINAL 2

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